



<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No.	Application No.:
	LAM1P185/P1228	10/758,637
	Applicant:	
	RAMALINGAM et al.	
Filing Date	Group	
January 14, 2004	1765	

### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
ll	A	6,001,742	12/14/99	Chang			05/07/98
ll	B	6,309,927 B1	10/30/01	Au et al.			03/05/99
ll	C	6,436,838 B1	08/20/02	Ying et al.			04/21/00

### Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
	D	08222238	03/06/98	Japan	H01L	21/768	Abs.	

### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	E	International Search Report and Written Opinion dated July 1, 2005 from corresponding International Application No. PCT/US2005/001073
	F	Kanniainen T. et al., "Growth of Dielectric HfO <sub>2</sub> /Ta <sub>2</sub> O <sub>5</sub> Thin Film Nanolaminate Capacitors by Atomic Layer Epitaxy", Electrochemical Society Proceedings, Electrochemical Society, Pennington, N.J., U.S., August 31, 1997, pages 36-46
Examiner	ll	Date Considered 2/2/06

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.